

AMENDMENT TO THE CLAIMS

Please **ADD** claims 16 and 17 as shown below.

Please **AMEND** claims 5-9 as shown below.

The following is a listing of the claims in this application:

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1. (Previously Amended) A method of reducing film growth rate when growing a carbon- or boron-doped silicon film or silicon-germanium film, comprising:
carbon or boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, at a temperature of below about 800°C, wherein said step of doping while supplying includes supplying a dopant precursor from a single source to the substrate at a substantially constant flow rate while lowering a flow rate of the silicon precursor, whereby a concentration of the dopant in the substrate increases.
 - c\ 2. (Original) The method of Claim 1, including supplying germanium precursor to the substrate.
 3. (Original) The method of Claim 1, wherein the film has a dopant content of about 1×10^{17} to $1 \times 10^{21} / \text{cm}^3$.
 4. (Original) The method of Claim 1, wherein the doping is at a temperature of less than 800°C.
 5. (Currently Amended) The A method according to claim 1, wherein the dopant is carbon.
 6. (Currently Amended) The A method according to claim 2, wherein the dopant is carbon..
 7. (Currently Amended) The A method according to claim 6, wherein the carbon doping is by a carbon precursor supply that is a single source.

8. (Currently Amended) The A method according to claim 2, wherein the film has a germanium content of 1 to 30% by weight.

9. (Currently Amended) The A method according to Claim 1, wherein the silicon precursor is silane supplied at a partial pressure in a range of about 0.1 to 10 millitorr.

10-14 (Withdrawn).

15. (Previously Amended) A method of growing a film without sharp pressure transitions, comprising:

cl carbon or boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduce pressure of about 0.1 to 100 millitorr.

16 (Added) The method of claim 1, wherein the step of carbon or boron doping comprised carbon and boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, at a temperature of below about 800°C, wherein said step of doping while supplying includes supplying a dopant precursor from a single source to the substrate at a substantially constant flow rate while lowering a flow rate of the silicon precursor, whereby a concentration of the dopant in the substrate increases.

17. (Added) The method of claim 15, wherein the step of carbon or boron-doping comprises carbon and boron-doping while supplying a silicon precursor and optionally a germanium precursor to a substrate, at reduced pressure of about 0.1 to 100 millitorr, at a temperature of below about 800°C, wherein said step of doping while supplying includes supplying a dopant precursor from a single source to the substrate at a substantially constant flow rate while lowering a flow rate of the silicon precursor, whereby a concentration of the dopant in the substrate increases.
